MPSA14 is a Preferred Device

Darlington Transistors

NPN Silicon

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CES}	30	Vdc
Collector - Base Voltage	V _{CBO}	30	Vdc
Emitter-Base Voltage	V _{EBO}	10	Vdc
Collector Current – Continuous	Ic	500	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

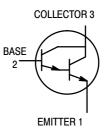
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/mW
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/mW

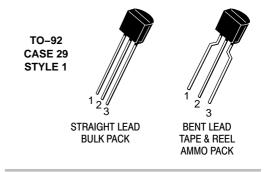
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



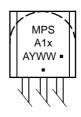
ON Semiconductor®

http://onsemi.com





MARKING DIAGRAM



x = 3 or 4

A = Assembly Location

Y = Year

WW = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS	•				ı
Collector – Emitter Breakdown Voltage ($I_C = 100 \mu Adc, I_B = 0$)		V _{(BR)CES}	30	-	Vdc
Collector Cutoff Current (V _{CB} = 30 Vdc, I _E = 0)		I _{CBO}	-	100	nAdc
Emitter Cutoff Current (V _{EB} = 10 Vdc, I _C = 0)		I _{EBO}	-	100	nAdc
ON CHARACTERISTICS (Note 1)			•		•
DC Current Gain ($I_C = 10 \text{ mAdc}$, $V_{CE} = 5.0 \text{ Vdc}$) ($I_C = 100 \text{ mAdc}$, $V_{CE} = 5.0 \text{ Vdc}$)	MPSA13 MPSA14 MPSA13 MPSA14	h _{FE}	5,000 10,000 10,000 20,000	- - -	-
Collector – Emitter Saturation Voltage (I _C = 100 mAdc, I _B = 0.1 mAdc)		V _{CE(sat)}	-	1.5	Vdc
Base – Emitter On Voltage (I _C = 100 mAdc, V _{CE} = 5.0 Vdc)		V _{BE(on)}	-	2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS			•		•
Current–Gain – Bandwidth Product (Note 2) (I _C = 10 mAdc, V _{CE} = 5.0 Vdc, f = 100 MHz)		f _T	125	_	MHz

^{1.} Pulse Test: Pulse Width $\leq 300 \,\mu\text{s}$; Duty Cycle $\leq 2.0\%$.

ORDERING INFORMATION

Device	Package	Shipping [†]
MPSA13	TO-92	5000 Units / Bulk
MPSA13G	TO-92 (Pb-Free)	5000 Units / Bulk
MPSA13RLRA	TO-92	2000 / Tape & Reel
MPSA13RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel
MPSA13RLRMG	TO-92 (Pb-Free)	2000 / Ammo Pack
MPSA13RLRPG	TO-92 (Pb-Free)	2000 / Ammo Pack
MPSA13ZL1G	TO-92 (Pb-Free)	2000 / Ammo Pack
MPSA14G	TO-92 (Pb-Free)	5000 Units / Bulk
MPSA14RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel
MPSA14RLRPG	TO-92 (Pb-Free)	2000 / Ammo Pack

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{2.} $f_T = |h_{fe}| \cdot f_{test}$.

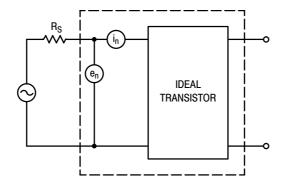


Figure 1. Transistor Noise Model

NOISE CHARACTERISTICS

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}C)$

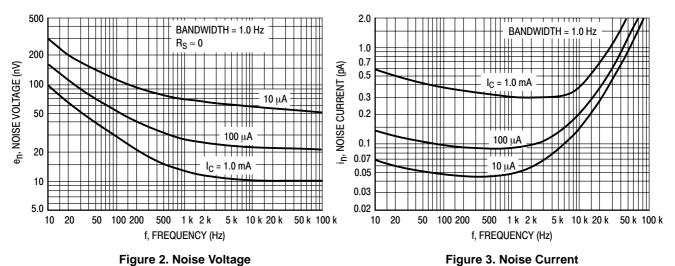


Figure 2. Noise Voltage

BANDWIDTH = 10 Hz TO 15.7 kHz

100 μΑ

1.0 mA

200

100

70

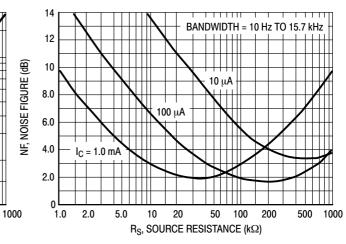
50

30

20

10 1.0 2.0

V_T, TOTAL WIDEBAND NOISE VOLTAGE (nV)



 R_S , SOURCE RESISTANCE ($k\Omega$) Figure 4. Total Wideband Noise Voltage

50

100

Figure 5. Wideband Noise Figure

SMALL-SIGNAL CHARACTERISTICS

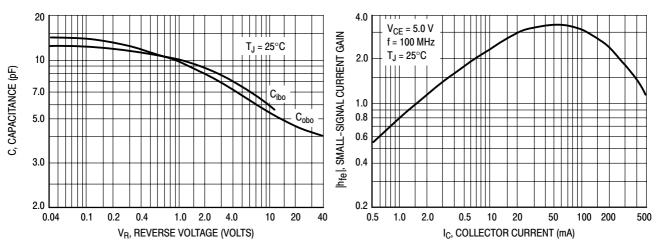


Figure 6. Capacitance

Figure 7. High Frequency Current Gain

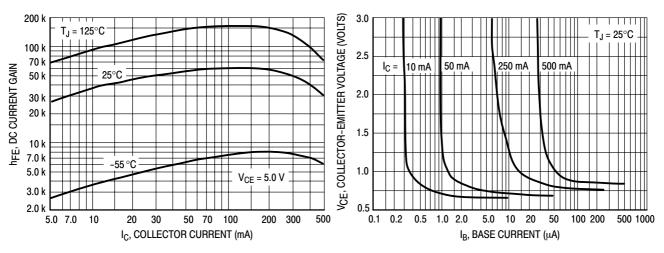


Figure 8. DC Current Gain

Figure 9. Collector Saturation Region

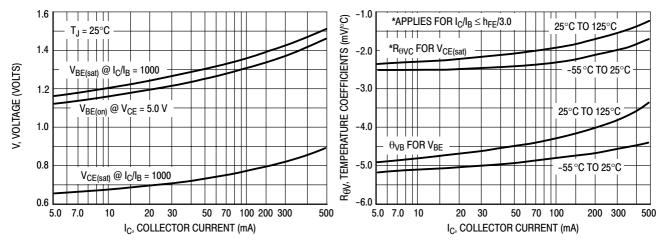


Figure 10. "On" Voltages

Figure 11. Temperature Coefficients

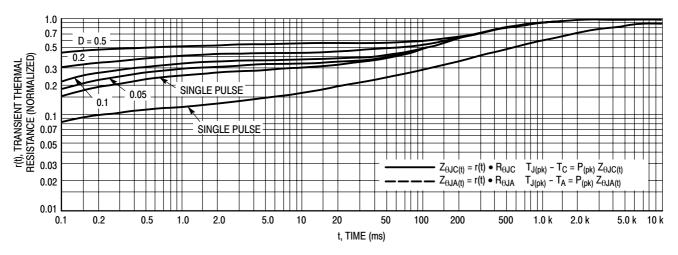


Figure 12. Thermal Response

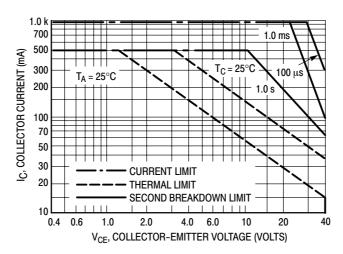
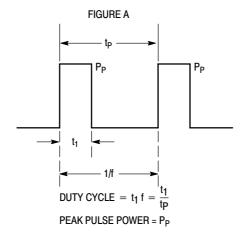
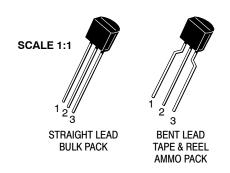


Figure 13. Active Region Safe Operating Area



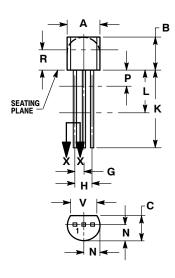
Design Note: Use of Transient Thermal Resistance Data





TO-92 (TO-226) CASE 29-11 **ISSUE AM**

DATE 09 MAR 2007



STRAIGHT LEAD **BULK PACK**



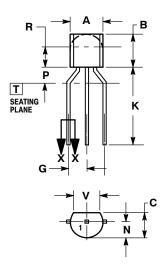
- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: INCH.

 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
7	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
V	0 135		3 43	



BENT LEAD TAPE & REEL AMMO PACK



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

- - MILLIMETERS
 MIN MAX DIM A B 4.45 5.20 5.33 4.19 4.32 C D 3.18 0.40 0.54 G 2.40 2.80 0.39 0.50 12.70 2.04 1.50 2.93 2.66 N Р 4.00

3.43

STYLES ON PAGE 2

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TO-92 (TO-226) CASE 29-11

ISSUE AM

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STYLE 1: PIN 1. 2. 3.	EMITTER BASE COLLECTOR	STYLE 2: PIN 1. 2. 3.	BASE EMITTER COLLECTOR	STYLE 3: PIN 1. 2. 3.	ANODE ANODE CATHODE	STYLE 4: PIN 1. 2. 3.	CATHODE CATHODE ANODE	STYLE 5: PIN 1. 2. 3.	DRAIN SOURCE GATE
STYLE 6: PIN 1. 2. 3.	GATE SOURCE & SUBSTRATE DRAIN	STYLE 7: PIN 1. 2. 3.	SOURCE DRAIN GATE	STYLE 8: PIN 1. 2. 3.	DRAIN GATE SOURCE & SUBSTRATE	STYLE 9: PIN 1. 2. 3.	BASE 1 EMITTER BASE 2	STYLE 10: PIN 1. 2. 3.	CATHODE GATE
STYLE 11: PIN 1. 2. 3.	ANODE CATHODE & ANODE CATHODE	STYLE 12: PIN 1. 2. 3.	MAIN TERMINAL 1 GATE MAIN TERMINAL 2	STYLE 13: PIN 1. 2. 3.	ANODE 1 GATE CATHODE 2	STYLE 14: PIN 1. 2. 3.	EMITTER COLLECTOR BASE	PIN 1. 2.	
2.	ANODE GATE CATHODE	2.	BASE	2.	ANODE CATHODE NOT CONNECTED	2.	ANODE	2.	NOT CONNECTED
PIN 1. 2.	COLLECTOR	PIN 1. 2.	SOURCE GATE DRAIN	STYLE 23: PIN 1. 2. 3.	GATE SOURCE DRAIN	STYLE 24: PIN 1. 2. 3.	EMITTER COLLECTOR/ANODE CATHODE		MT 1 GATE
		2.	MT SUBSTRATE MT	2.		PIN 1. 2.	ANODE	STYLE 30: PIN 1. 2. 3.	DRAIN GATE
	GATE	PIN 1. 2.	BASE COLLECTOR EMITTER	STYLE 33: PIN 1. 2. 3.	RETURN	2.			

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